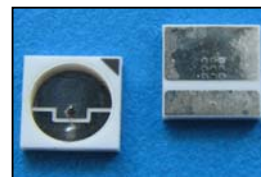




## LED36-SMD5



### TECHNICAL DATA

### Mid-Infrared Light Emitting Diode, SMD

Light Emitting Diodes with central wavelength 3.65  $\mu\text{m}$  series are based on heterostructures grown on InAs substrates by MOCVD. InAsSb is used in the active layer. Wide band gap solid solutions InAsSbP with P content 50% are used for good electron confinement.

LED36-SMD5 has a stable output power and a lifetime more than 80000 hours.

#### Features

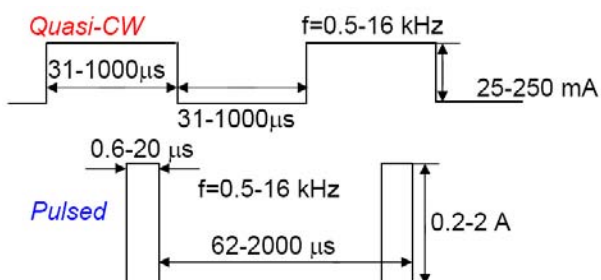
- Structure: InAsSb/InAsSbP
- Peak Wavelength: typ. 3.65  $\mu\text{m}$
- Optical Output Power: typ. 30  $\mu\text{W}$  qCW
- Package: SMD 5x5 mm



#### Specifications

Item	Condition	Rating			Unit
		Min.	Typ.	Max.	
Peak Wavelength	T=300 K	3.60	3.65	3.70	$\mu\text{m}$
FWHM	150 mA CW	0.40	0.50	0.60	$\mu\text{m}$
Quasi-CW Optical Power	200 mA qCW	20	30	40	$\mu\text{W}$
Pulsed Optical Power	1 A	180	200	220	$\mu\text{W}$
Switching Time	T=300 K	10	20	30	ns
Operation Voltage	200 mA qCW				V
Operating Temperature	-240 ... +50				$^{\circ}\text{C}$
Emitting Area	300x300				$\mu\text{m}$
Soldering Temperature	180				$^{\circ}\text{C}$
Package	SMD type package 5x5 mm based on high thermal conductivity ceramics				

#### Operating Regime



#### Quasi-CW

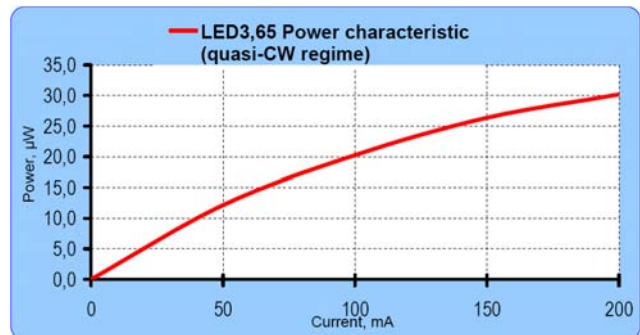
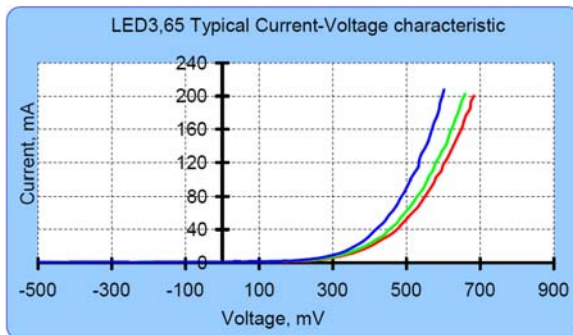
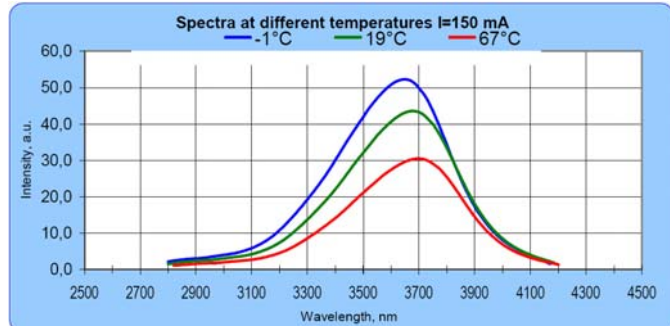
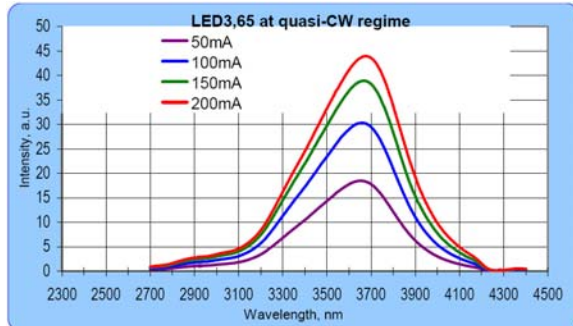
- Maximum current 220 mA
- Recommended current 150-200mA

#### Pulsed

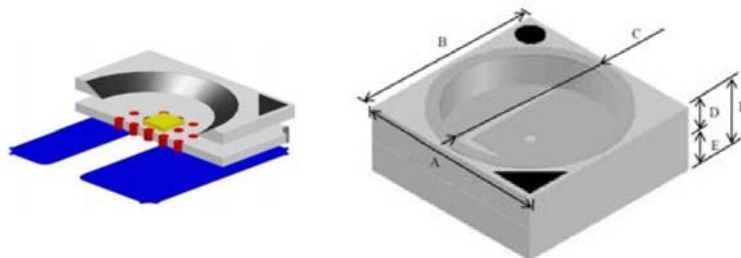
- Maximum current 1 A (puls length 500 ns, repetition rate 2kHz)



## Typical Performance Curves



## Package



ITEM	Symbol	Rule
Basic Outline	A	5.0 ± 0.1mm
Basic Outline	B	5.0 ± 0.1mm
Cavity size	C	Max 4.2Φ
Top layer	D	Min 0.4mm
Bottom layer	E	Min 0.4mm
Thickness	F	Max 2mm

- Tiny package for surface mounting
- Anode and cathode are led to the metalized areas on the back side of the ceramic surface
- Material – Low Temperature Co-fired Ceramic (LTCC):
  - thermal conductivity 25 W/mK
  - thermoresistance 8 °C/W